

E1.S 4TG2-P



HIGHLIGHT FEATURES

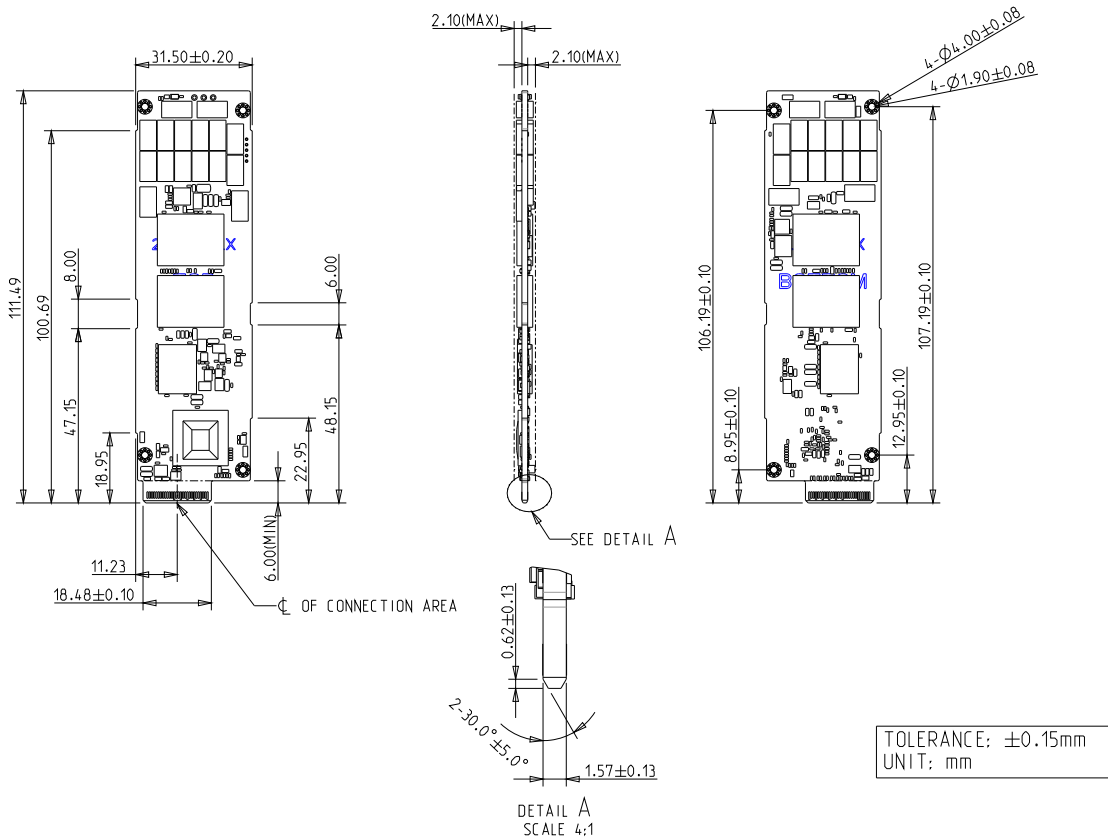
- PCIe Gen 4 x4, NVMe 1.4
- PLP (iCell) technology for power loss protection
- Stable sustained performance
- LDPC ECC engine supported
- Dynamic Thermal Management

SPECIFICATIONS

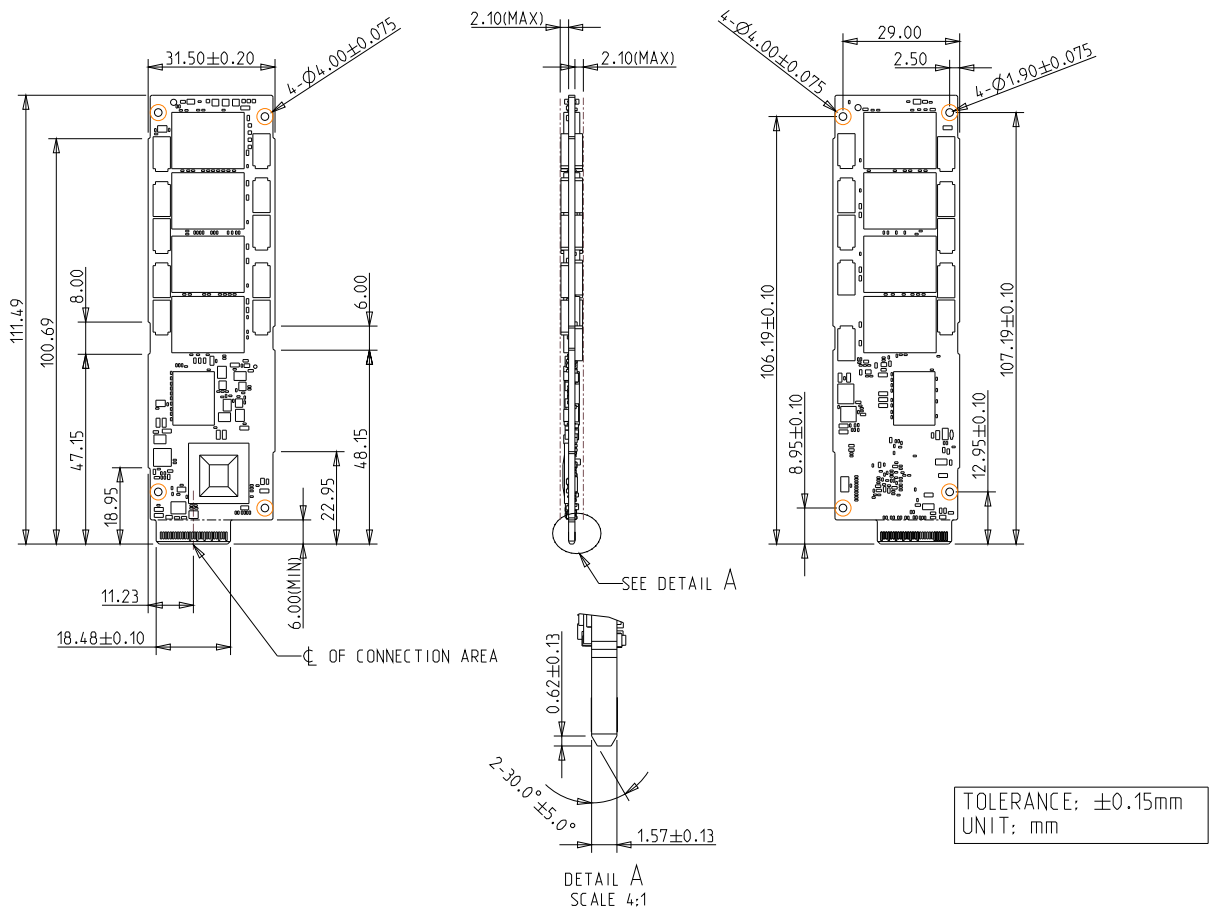
Model Name	E1.S 4TG2-P
Flash Type	3D TLC
Interface	PCIe Gen 4 x4
Form Factor	E1.S
Capacity	512GB ~ 8TB
Sequential R / W (MB/sec, max.)	6,900 / 4,700
P/E Cycle	3,000
TBW (Max.)	19,129
Storage Temperature	-40°C ~ 85°C
Max. Power Consumption	12W
Max. Channels	8
External DRAM Buffer	Y
H/W Write Protect	N
S.M.A.R.T.	Y
AES	Y
TCG Opal	Y
Dimension (W x L x H/mm)	5.9mm : 31.5 x 111.5 x 5.9 9.5mm : 33.75 x 118.75 x 9.5 15mm : 33.75 x 118.75 x 15.0
Vibration	20G@[7 ~ 2000Hz]
Shock	1500G@0.5ms
MTBF	>3 million hours
Warranty	3 Years

DIAGRAM

5.9mm (512GB ~ 4TB)

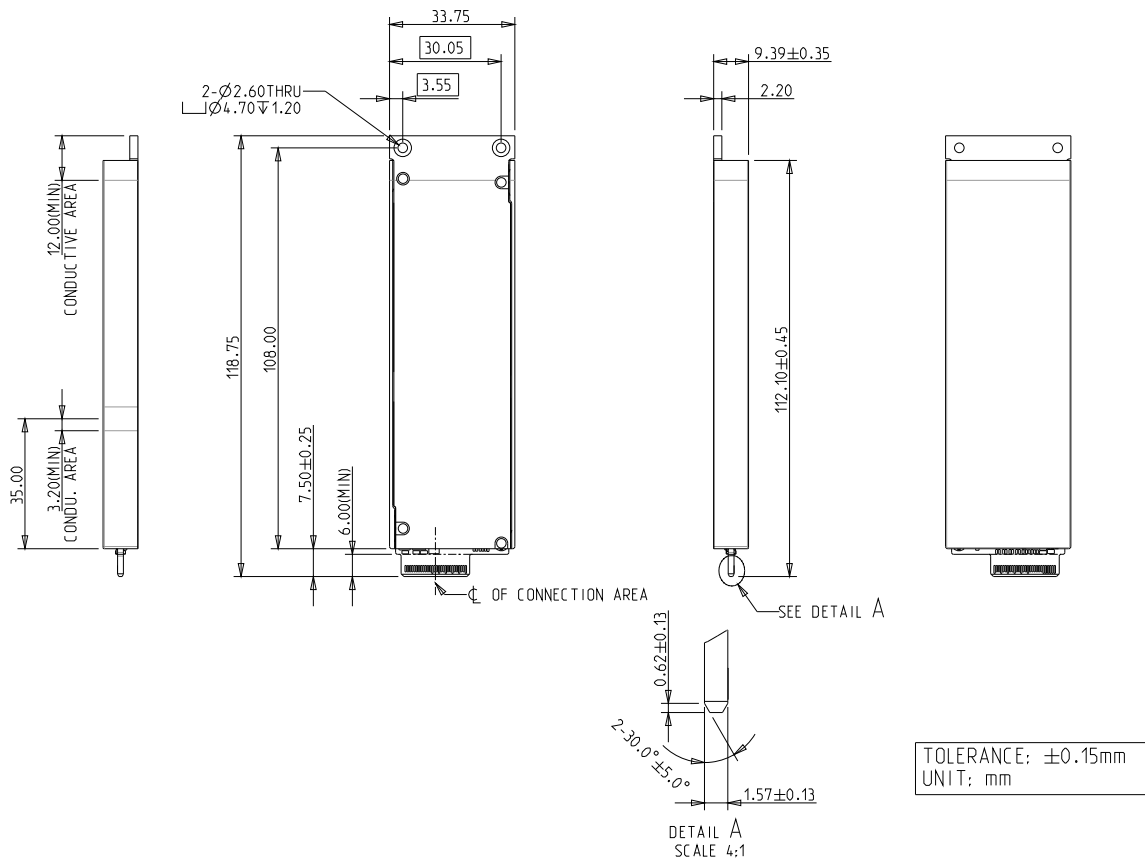


5.9mm (8TB)

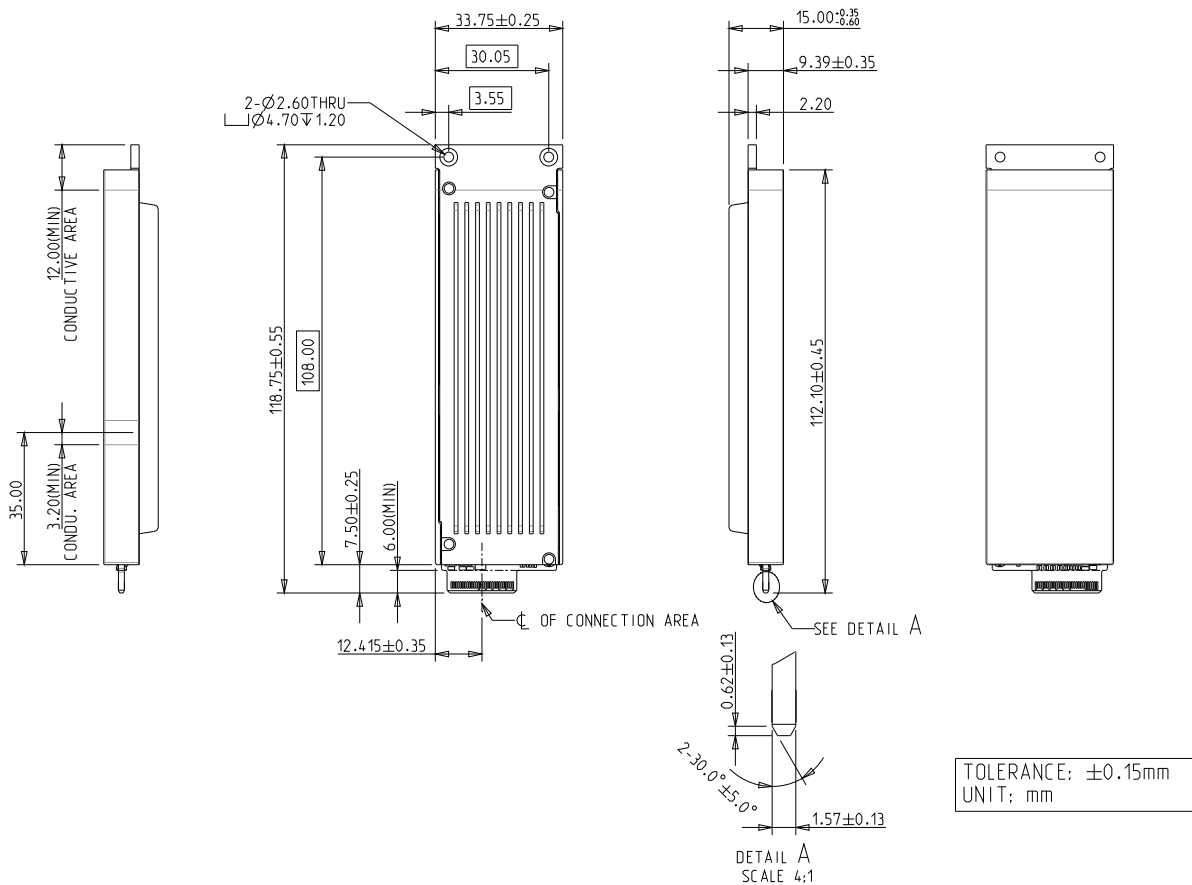


DIAGRAM

9.5mm



15mm



ORDER INFO.

Operating Temperature	Standard Grade (0°C ~ 70°C)	Industrial Grade (-40°C ~ 85°C)
512GB	DGE1S-C12DP2KCAEFP%	DGE1S-C12DP2KWAEFP%
1TB	DGE1S-01TDP2KCAEFP%	DGE1S-01TDP2KWAEFP%
2TB	DGE1S-02TDP2KCAEFP%	DGE1S-02TDP2KWAEFP%
4TB	DGE1S-04TDP2KCAEFP%	DGE1S-04TDP2KWAEFP%
8TB	DGE1S-08TDP2KCBEP%	DGE1S-08TDP2KWBEFP%

Operation temperature based on temperature obtained from S.M.A.R.T.
 % : Non-existent = 5.9mm / H = 9.5mm enclosure / H1 = 15mm enclosure
 E1.S 4TG2-P specifications are subject to change.

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